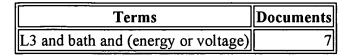
### **Refine Search**





US Pre-Grant Publication Full-Text Database

# US Patents Full-Text Database US OCR Full-Text Database

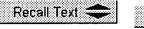
Database:

EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

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### Search History

DATE: Thursday, March 03, 2005 Printable Copy Create Case

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DB=U	SPT; PLUR=YES; OP=ADJ		
<u>L4</u>	L3 and bath and (energy or voltage)	7	<u>L4</u>
<u>L3</u>	L1 and hydrophobic	69	<u>L3</u>
<u>L2</u>	L1 near5 hydrophobic	0	<u>L2</u> .

copper near4 (encased or embedded)

**END OF SEARCH HISTORY** 

L1

### **Hit List**

**Generate Collection** Print Fwd Refs Bkwd Refs Clear Generate OACS

**Search Results -** Record(s) 1 through 7 of 7 returned.

☐ 1. Document ID: US 6709555 B1

L4: Entry 1 of 7

File: USPT

Mar 23, 2004

US-PAT-NO: 6709555

DOCUMENT-IDENTIFIER: US 6709555 B1

\*\* See image for Certificate of Correction \*\*

TITLE: Plating method, interconnection forming method, and apparatus for carrying

out those methods

Full Title Offstion Front Review Classification Date Reference ☐ 2. Document ID: US 6261433 B1

L4: Entry 2 of 7

File: USPT

Jul 17, 2001

US-PAT-NO: 6261433

DOCUMENT-IDENTIFIER: US 6261433 B1

\*\* See image for Certificate of Correction \*\*

TITLE: Electro-chemical deposition system and method of electroplating on

substrates

Claims KMC Draw De Full Title Citation Front Review Classification Data Reference

☐ 3. Document ID: US 5167857 A

L4: Entry 3 of 7

File: USPT

Dec 1, 1992

US-PAT-NO: 5167857

DOCUMENT-IDENTIFIER: US 5167857 A

\*\* See image for Certificate of Correction \*\*

TITLE: Lactic acid derivative, liquid crystal composition containing same and

liquid crystal device

ROU Title Citation Front Review Classification Date Reference Claims 10000 Drave De

☐ 4. Document ID: US 5143643 A

L4: Entry 4 of 7

File: USPT

Sep 1, 1992

US-PAT-NO: 5143643

DOCUMENT-IDENTIFIER: US 5143643 A

\*\* See image for Certificate of Correction \*\*

TITLE: Optically active mesomorphic compound

Full Title Chation Front Review Classification Date Reference Claims 10000 Draw D. ☐ 5. Document ID: US 5114613 A L4: Entry 5 of 7 File: USPT May 19, 1992 US-PAT-NO: 5114613 DOCUMENT-IDENTIFIER: US 5114613 A TITLE: Lactic acid derivative and liquid crystal composition containing same Full Title Citation Front Review Classification Date Reference ☐ 6. Document ID: US 4882085 A L4: Entry 6 of 7 File: USPT Nov 21, 1989 US-PAT-NO: 4882085 DOCUMENT-IDENTIFIER: US 4882085 A \*\* See image for Certificate of Correction \*\* TITLE: Lactic acid derivative and liquid crystal composition containing same

Full Title Citation Front Review Classification Date Reference Claims 1000 Draw D. ☐ 7. Document ID: US 4775223 A

L4: Entry 7 of 7

File: USPT

Oct 4, 1988

US-PAT-NO: 4775223

DOCUMENT-IDENTIFIER: US 4775223 A

\*\* See image for <u>Certificate of Correction</u> \*\*

TITLE: Lactic acid derivative, liquid crystal composition containing same and

liquid crystal device

Full Title Citation Front Review Classification Date Reference Clear Generate Collection Print Fwd Refs Bkwd Refs Generate OACS Terms Documents L3 and bath and (energy or voltage)

Display Format: TI

Change Format

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### **Refine Search**

#### Search Results -

Terms	Documents
L12 and copper	2

US Pre-Grant Publication Full-Text Database

# US Patents Full-Text Database US OCR Full-Text Database

Database:

JPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

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### Search History

DATE: Thursday, March 03, 2005 Printable Copy Create Case

Set Name side by sid		Hit Count	Set Name result set
•	SPT; PLUR=YES; OP=ADJ		
<u>L13</u>	L12 and copper	2	<u>L13</u>
<u>L12</u>	L10 and interlayer	8	<u>L12</u>
<u>L11</u>	L10 and interlayer and electroless	0	<u>L11</u>
<u>L10</u>	cobalt near3 (capping adj layer)	44	<u>L10</u>
<u>L9</u>	L7 and interlayer and dielectric and copper	0	<u>L9</u>
<u>L8</u>	L7 and electroless	1	<u>L8</u>
<u>L7</u>	ultra adj sonic adj energy	84	<u>L7</u>
<u>L6</u>	L1 and (sonic adj energy)	0	<u>L6</u>
<u>L5</u>	L1 and capping	0	<u>L5</u>
<u>L4</u>	L1 and (cobalt near2 capping)	0	<u>L4</u>
<u>L3</u>	L1 and copper	4	<u>L3</u>
<u>L2</u>	L1 and (plurality near5 copper)	0	<u>L2</u>
<u>L1</u>	hydrophobic near2 interlayer	22	<u>L1</u>

WEST Refine Search Page 2 of 2

END OF SEARCH HISTORY

'Record List Display Page 1 of 1

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<u>Clear</u> <u>G</u>	enerate Collection Print Generate OAC		wd Refs
Sea	rch Results - Record(s) 1 thre	ough 2 of 2 returned.	
☐ 1. Document ID: L13: Entry 1 of 2	US 6853049 B2 File: USP	т	Feb 8, 2005
US-PAT-NO: 6853049 DOCUMENT-IDENTIFIER: US	6853049 B2		
TITLE: Silicide-silicon	oxide-semiconductor ant	ifuse device and met	chod of making
Full   Title   Citation   Front	Review Classification Date Refere	1762	Claims   KMC   Draw D
☐ 2. Document ID:	US 6268985 B1 File: USPT	,	Jul 31, 2001
US-PAT-NO: 6268985 DOCUMENT-IDENTIFIER: US	6268985 B1		
TITLE: Read head having	spin valve sensor with	improved capping lay	/er
Full   Title   Citation   Front	Review Classification Cate Refere	1023	Glaims RWC (Glave D
Clear Generate Col	lection Print Fwd Re	efs Bkwd Refs	Generate OACS
Terms L12 and copper		Documents	2
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### Hit List

Generate Collection Fwd Refs **Bkwd Refs** Clear Print Generate OACS

Search Results - Record(s) 1 through 4 of 4 returned.

☐ 1. Document ID: US 6815207 B2

L3: Entry 1 of 4

Nov 9, 2004

US-PAT-NO: 6815207

DOCUMENT-IDENTIFIER: US 6815207 B2

TITLE: Moisture/wetness detecting method, moisture/wetness detecting label, articles with moisture/wetness detecting function, and detecting material and

method

Fill Title Castion Front Review Classification Date Reference Claims Ruce Oracle ☐ 2. Document ID: US 5866287 A

L3: Entry 2 of 4

File: USPT

Feb 2, 1999

US-PAT-NO: 5866287

DOCUMENT-IDENTIFIER: US 5866287 A

TITLE: Imaging element comprising and electrically-conductive layer containing

metal antimonate and non-conductive metal-containing colloidal particles

Full Title Citation Front Review Classification Date Reference Claims KWW Draw De

☐ 3. Document ID: US 3880657 A

L3: Entry 3 of 4

File: USPT

Apr 29, 1975

US-PAT-NO: 3880657

DOCUMENT-IDENTIFIER: US 3880657 A

\*\* See image for Certificate of Correction \*\*

TITLE: Conducting layer for organic photoconductive element

Full Title Citation Front Review Classification Cate Reference

☐ 4. Document ID: US 3559576 A

L3: Entry 4 of 4

File: USPT

Feb 2, 1971

US-PAT-NO: 3559576

DOCUMENT-IDENTIFIER: US 3559576 A

TITLE: PLANOGRAPHIC REVERSED PRINTING

Full Title: Citation Front: Review	Classification   Date   Reference	Clains   1900   Draw U
Clear Generate Collection	Print Fwd Refs B	kwd Refs Generate OACS
L1 and copper	Documents	4

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Previous Page Go to Doc# Next Page

## **Hit List**

Clear Generate Collection Print Generate OACS	Fwd Refs	Bkwd Refs
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Search Results - Record(s) 1 through 1 of 1 returned.

☐ 1. Document ID: US 6846725 B2

L8: Entry 1 of 1 File: USPT

Jan 25, 2005

US-PAT-NO: 6846725

DOCUMENT-IDENTIFIER: US 6846725 B2

TITLE: Wafer-level package for micro-electro-mechanical systems

Full   Title   Citation   Front   Review   Classification	Option References Options Note:	(b)
Clear Generate Collection Print	Fwd Refs Bkwd Refs Generate OACS	
		*****
Terms	Documents	
L7 and electroless	1	

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### Refine Search

#### Search Results -

Terms	Documents
L14 and cobalt	0

US Pre-Grant Publication Full-Text Database

# US Patents Full-Text Database US OCR Full-Text Database

Database:

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JPO Abstracts Database
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### Search History

DATE: Thursday, March 03, 2005 Printable Copy Create Case

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DB=U	SPT; PLUR=YES; OP=ADJ		
<u>L17</u>	L14 and cobalt	0	<u>L17</u>
<u>L16</u>	L14 and (cu or copper) and cobalt	0	<u>L16</u>
<u>L15</u>	L14 and copper	3	<u>L15</u>
<u>L14</u>	L7 and dielectric	8	<u>L14</u>
<u>L13</u>	L12 and copper	2	<u>L13</u>
<u>L12</u>	L10 and interlayer	8	<u>L12</u>
<u>L11</u>	L10 and interlayer and electroless	0	<u>L11</u>
<u>L10</u>	cobalt near3 (capping adj layer)	44	<u>L10</u>
<u>L9</u>	L7 and interlayer and dielectric and copper	. 0	<u>L9</u>
<u>L8</u>	L7 and electroless	1	<u>L8</u>
<u>L7</u>	ultra adj sonic adj energy	84	<u>L7</u>
<u>L6</u>	L1 and (sonic adj energy)	0	<u>L6</u>
<u>L5</u>	L1 and capping	0	<u>L5</u>
<u>L4</u>	L1 and (cobalt near2 capping)	0	<u>L4</u>

<u>L3</u>	L1 and copper	4	<u>L3</u>
<u>L2</u>	L1 and (plurality near5 copper)	0	<u>L2</u>
<u>L1</u>	hydrophobic near2 interlayer	22	<u>L1</u>

### END OF SEARCH HISTORY

_	Hit List	
Clear Generate Col	llection Print Ewd Re Generate OACS	fs Bkwd Refs
Search Resul	ts - Record(s) 1 through 3 of 3 re	eturned.
☐ 1. Document ID: US 68467	725 B2	
L15: Entry 1 of 3	File: USPT	Jan 25, 2005
US-PAT-NO: 6846725 DOCUMENT-IDENTIFIER: US 6846725	B2	
TITLE: Wafer-level package for m	micro-electro-mechanical s	ystems
Füll   Title   Citation   Front   Review   Cla	ssilication: Date Reference	Clains   KWC   Draw Dr
☐ 2. Document ID: US 43607		
L15: Entry 2 of 3	File: USPT	Nov 23, 1982
US-PAT-NO: 4360706 DOCUMENT-IDENTIFIER: US 4360706	A	
TITLE: Electric cables of reduce	ed micro-voids in the extr	uded insulation
Full   Title   Citation   Front   Review   Cla	scripation   Cate   Reference	Claims FMC Cysw. Co
☐ 3. Document ID: US 42592	281 A	
L15: Entry 3 of 3	File: USPT	Mar 31, 1981
US-PAT-NO: 4259281 DOCUMENT-IDENTIFIER: US 4259281 ** See image for Certificate of		
TITLE: Process for reducing microables	ro-voids in the extruded i	nsulation of electric
Full   Title   Chation   Front   Review   Ch	issinipation:     Dateii    Reference	Cisins DWC Urse, U-
Clear Generate Collection	Print Fwd Refs Bkw	d Refs Generate OACS
Terms	Documents	

L14 and copper

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### **Refine Search**

#### Search Results -

Terms	Documents
L22 and cobalt	0

US Pre-Grant Publication Full-Text Database
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JPO Abstracts Database
Derwent World Patents Index

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Search:

L23

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### Search History

DATE: Thursday, March 03, 2005 Printable Copy Create Case

Set Name Query side by side		Hit Count S	et Name result set
•	SPT; PLUR=YES; OP=ADJ		
<u>L23</u>	L22 and cobalt	0	<u>L23</u>
<u>L22</u>	L19 and electroless	5	<u>L22</u>
<u>L21</u>	L19 and (electroless near bath)	0	<u>L21</u>
<u>L20</u>	L19 and (ultra adj sonic adj energy)	0	<u>L20</u>
<u>L19</u>	L18 and (capping adj layer)	23	<u>L19</u>
<u>L18</u>	copper near7 interlayer	677	<u>L18</u>
<u>L17</u>	L14 and cobalt	0	<u>L17</u>
<u>L16</u>	L14 and (cu or copper) and cobalt	0	<u>L16</u>
<u>L15</u>	L14 and copper	3	<u>L15</u>
<u>L14</u>	L7 and dielectric	8	<u>L14</u>
<u>L13</u>	L12 and copper	2	<u>L13</u>
<u>L12</u>	L10 and interlayer	8	<u>L12</u>
<u>L11</u>	L10 and interlayer and electroless	0	<u>L11</u>
<u>L10</u>	cobalt near3 (capping adj layer)	44	<u>L10</u>

WEST Refine Search Page 2 of 2

<u>L9</u>	L7 and interlayer and dielectric and copper	0	<u>L9</u>
<u>L8</u>	L7 and electroless	1	<u>L8</u>
<u>L7</u>	ultra adj sonic adj energy	84	<u>L7</u>
<u>L6</u>	L1 and (sonic adj energy)	0	<u>L6</u>
<u>L5</u>	L1 and capping	0	<u>L5</u>
<u>L4</u>	L1 and (cobalt near2 capping)	0	<u>L4</u>
<u>L3</u>	L1 and copper	4	<u>L3</u>
<u>L2</u>	L1 and (plurality near5 copper)	0	<u>L2</u>
Ll	hydrophobic near2 interlayer	22	Ll

## END OF SEARCH HISTORY

Record List Display Page 1 of 2

### **Hit List**

Clear Generate Collection Print Fwd Refs Bkwd Refs
Generate OACS

**Search Results -** Record(s) 1 through 5 of 5 returned.

☐ 1. Document ID: US 6800554 B2

L22: Entry 1 of 5

File: USPT

Oct 5, 2004

US-PAT-NO: 6800554

DOCUMENT-IDENTIFIER: US 6800554 B2

TITLE: Copper alloys for interconnections having improved electromigration

characteristics and methods of making same

Full Title Craim Front Review Classification Date Reference Claims 1240C 12200 C

US-PAT-NO: 6562416

DOCUMENT-IDENTIFIER: US 6562416 B2

TITLE: Method of forming low resistance vias

☐ 3. Document ID: US 6486055 B1

L22: Entry 3 of 5 File: USPT Nov 26, 2002

US-PAT-NO: 6486055

DOCUMENT-IDENTIFIER: US 6486055 B1

TITLE: Method for forming copper interconnections in semiconductor component using

electroless plating system

4. Document ID: US 6462417 B1

US-PAT-NO: 6462417

DOCUMENT-IDENTIFIER: US 6462417 B1

Record List Display Page 2 of 2

TITLE: Coherent alloy diffusion barrier for integrated circuit interconnects

Full	assification   Date: Reference	Bisims III ROMBIII III OTSAGO.
☐ 5. Document ID: US 64456	070 B1	
L22: Entry 5 of 5	File: USPT	Sep 3, 2002

US-PAT-NO: 6445070

DOCUMENT-IDENTIFIER: US 6445070 B1

TITLE: Coherent carbide diffusion barrier for integrated circuit interconnects

Full. Title Citation Front Review Classification	Date References Claims Konce Draw D
Clear Generate Collection Print	Fwd Refs Bkwd Refs Generate OACS
Terms	Documents
L19 and electroless	5

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### Refine Search

#### Search Results -

Terms	Documents
L30 and cobalt	4

US Pre-Grant Publication Full-Text Database

### US Patents Full-Text Database

Database:

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#### Search History

DATE: Thursday, March 03, 2005 Printable Copy Create Case

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DB=U	SPT; PLUR=YES; OP=ADJ		
<u>L31</u>	L30 and cobalt	4	<u>L31</u>
<u>L30</u>	L25 and electroless	4	<u>L30</u>
<u>L29</u>	L25 and power	5	<u>L29</u>
<u>L28</u>	L25 and watts	0	<u>L28</u>
<u>L27</u>	L25 and hertz	0	<u>L27</u>
<u>L26</u>	L25 and (sonic adj energy)	0	<u>L26</u>
<u>L25</u>	L24 and interlayer	11	<u>Ľ25</u>
<u>L24</u>	copper near9 hydrophobic	205	<u>L24</u>
<u>L23</u>	L22 and cobalt	0	<u>L23</u>
<u>L22</u>	L19 and electroless	5	<u>L22</u>
<u>L21</u>	L19 and (electroless near bath)	0	<u>L21</u>
<u>L20</u>	L19 and (ultra adj sonic adj energy)	. 0	<u>L20</u>
<u>L19</u>	L18 and (capping adj layer)	23	<u>L19</u>
<u>L18</u>	copper near7 interlayer	677	<u>L18</u>

<u>L17</u>	L14 and cobalt	0	<u>L17</u>
<u>L16</u>	L14 and (cu or copper) and cobalt	0	<u>L16</u>
<u>L15</u>	L14 and copper	3	<u>L15</u>
<u>L14</u>	L7 and dielectric	8	<u>L14</u>
<u>L13</u>	L12 and copper	2	<u>L13</u>
<u>L12</u>	L10 and interlayer	8	<u>L12</u>
<u>L11</u>	L10 and interlayer and electroless	0	<u>L11</u>
<u>L10</u>	cobalt near3 (capping adj layer)	44	<u>L10</u>
<u>L9</u>	L7 and interlayer and dielectric and copper	0	<u>L9</u>
<u>L8</u>	L7 and electroless	1	<u>L8</u>
<u>L7</u>	ultra adj sonic adj energy	84	<u>L7</u>
<u>L6</u>	L1 and (sonic adj energy)	0	<u>L6</u>
<u>L5</u>	L1 and capping	0	<u>L5</u>
<u>L4</u>	L1 and (cobalt near2 capping)	0	<u>L4</u>
<u>L3</u>	L1 and copper	4	<u>L3</u>
<u>L2</u>	L1 and (plurality near5 copper)	0	<u>L2</u>
L1	hydrophobic near2 interlayer	22	L1

### END OF SEARCH HISTORY

### **Hit List**

Clear Generate Collection Print Fwd Refs Bkwd Refs

Generate OACS

**Search Results -** Record(s) 1 through 4 of 4 returned.

☐ 1. Document ID: US 6838772 B2

L31: Entry 1 of 4

File: USPT

Jan 4, 2005

US-PAT-NO: 6838772

DOCUMENT-IDENTIFIER: US 6838772 B2

TITLE: Semiconductor device

□ 2. Document ID: US 6730594 B2

L31: Entry 2 of 4 File: USPT May 4, 2004

US-PAT-NO: 6730594

DOCUMENT-IDENTIFIER: US 6730594 B2

TITLE: Method for manufacturing semiconductor device

☐ 3. Document ID: US 6723631 B2

L31: Entry 3 of 4 File: USPT Apr 20, 2004

US-PAT-NO: 6723631

DOCUMENT-IDENTIFIER: US 6723631 B2

TITLE: Fabrication method of semiconductor integrated circuit device

| Full | Title | Chaign | Front | Review | Classification | Date | Reference | Classification | Date |

US-PAT-NO: 3944440

DOCUMENT-IDENTIFIER: US 3944440 A

TITLE: Selective reflecting metal/metal oxide coatings using surfactant to promote

uniform oxidation

fülli	ille   Citation   Front   Review   Clas	sification   Date   Reference		Glaims   RMAC   Diave D
Clear	Generate Collection	Print I Fwd Refs	Bkwd Refs	Generate OACS
<u> </u>	Terms	Doc	cuments	
	L30 and cobalt			4

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# **PALM INTRANET**

18/84,592

Day: Thursday

Date: 3/3/2005 Time: 21:22:15

### **Inventor Name Search Result**

Your Search was:

Last Name = BRASK First Name = JUSTIN

Application#	Patent#	==			Inventor Name
<u>10808021</u>	Not Issued	030		STRAINED SILICON WITH REDUCED ROUGHNESS	BRASK, JUSTIN
10949994	Not Issued	020	09/23/2004	U-GATE TRANSISTORS AND METHODS OF FABRICATION	BRASK, JUSTIN
<u>10977261</u>	Not Issued	030	10/29/2004	RESONANT TUNNELING DEVICE USING METAL OXIDE SEMICONDUCTOR PROCESSING	BRASK, JUSTIN
10209843	6861005	150	07/31/2002	GENERATING NITRIDE WAVEGUIDES	BRASK, JUSTIN K.
10210461	6797622	150	07/31/2002	SELECTIVE ETCHING OF POLYSILICON	BRASK, JUSTIN K.
10242740	6770568	150	09/12/2002	SELECTIVE ETCHING USING SONICATION	BRASK, JUSTIN K.
10260591	<u>6746967</u>	150	09/30/2002	ETCHING METAL USING SONICATION	BRASK, JUSTIN K.
10271446	Not Issued	083	10/15/2002	PROTECTING DELICATE SEMICONDUCTOR FEATURES DURING WET ETCHING	BRASK, JUSTIN K.
10272624	Not Issued	083	10/17/2002	WET ETCHING NARROW TRENCHES	BRASK, JUSTIN K.
10273474	6743740	150	10/18/2002	USING SONIC ENERGY IN CONNECTION WITH LASER- ASSISTED DIRECT IMPRINTING	BRASK, JUSTIN K.
10278535	Not Issued	041	10/23/2002	REMOVING FLUORINE-BASED PLASMA ETCH RESIDUES	BRASK, JUSTIN K.
10294266	Not Issued	061	11/14/2002	CONTROLLED USE OF PHOTOCHEMICALLY SUSCEPTIBLE CHEMISTRIES FOR ETCHING, CLEANING AND SURFACE CONDITIONING	BRASK, JUSTIN K.

10295150	6624127	150		HIGHLY POLAR CLEANS FOR REMOVAL OF RESIDUES FROM SEMICONDUCTOR STRUCTURES	BRASK, JUSTIN K.
10301038	Not Issued	041	11/20/2002	OXIDATION INHIBITOR FOR WET ETCHING PROCESSES	BRASK, JUSTIN K.
10305684	Not Issued	083	11/26/2002	SACRIFICIAL ANNEALING LAYER FOR A SEMICONDUCTOR DEVICE AND A METHOD OF FABRICATION	BRASK, JUSTIN K.
10327293	6858483	150	12/20/2002	INTEGRATING N-TYPE AND P- TYPE METAL GATE TRANSISTORS	BRASK, JUSTIN K.
10338174	6709911	150	01/07/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
10382452	Not Issued	094	03/06/2003	ACOUSTIC STREAMING OF CONDENSATE DURING SPUTTERED METAL VAPOR DEPOSITION	BRASK, JUSTIN K.
10387303	6716707	150	03/11/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
10391816	6696327	150	03/18/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
10395447	6737365	150	03/24/2003	FORMING A POROUS DIELECTRIC LAYER	BRASK, JUSTIN K.
10397924	Not Issued	041	03/25/2003	REMOVING SILICON NANO- CRYSTALS	BRASK, JUSTIN K.
10421557	Not Issued	041	04/21/2003	METHOD AND APPARATUS FOR PARTICLE REMOVAL	BRASK, JUSTIN K.
10441616	6806146	150	05/20/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
10454109	Not Issued	030	06/04/2003	HIGHLY POLAR CLEANS FOR REMOVAL OF RESIDUES FROM SEMICONDUCTOR STRUCTURES	BRASK, JUSTIN K.
<u>10464016</u>	Not Issued	061	II .	CHEMICAL THINNING OF SILICON BODY OF AN SOI	BRASK, JUSTIN K.

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10607955	Not Issued	030	06/26/2003	SELECTIVE SURFACE EXPOSURE, CLEANS, AND CONDITIONING OF THE GERMANIUM FILM IN A GE PHOTODETECTOR	BRASK, JUSTIN K.
10608669	Not Issued	030	06/27/2003	USING BIDENTATE CHELATORS TO CLEAN SEMICONDUCTOR WAFERS	BRASK, JUSTIN K.
10622955	Not Issued	041	07/18/2003	ETCHING METAL SILICIDES AND GERMANIDES	BRASK, JUSTIN K.
10626336	Not Issued	061		FORMING A HIGH DIELECTRIC CONSTANT FILM USING METALLIC PRECURSOR	BRASK, JUSTIN K.
10629127	Not Issued	040	07/29/2003	PREVENTING SILICIDE FORMATION AT THE GATE ELECTRODE IN A REPLACEMENT METAL GATE TECHNOLOGY	BRASK, JUSTIN K.
10632470	6855639	150	II I	PRECISE PATTERNING OF HIGH-K FILMS	BRASK, JUSTIN K.
<u>10652546</u>	Not Issued	030	08/28/2003	SELECTIVE ETCH PROCESS FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
<u>10652796</u>	Not Issued	071	08/28/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K
10658225	Not Issued	030	09/08/2003	METHODS AND COMPOSITIONS FOR SELECTIVELY ETCHING METAL FILMS AND STRUCTURES	BRASK, JUSTIN K.
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10696204	Not Issued	071	10/29/2003	DEPOSITING AN OXIDE	BRASK, JUSTIN K.
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10704498	Not Issued	030	11/06/2003	METHOD FOR ETCHING A THIN METAL LAYER	BRASK, JUSTIN K.

<u>10716321</u>	Not Issued	092	11/17/2003	SACRIFICIAL ANNEALING LAYER FOR A SEMICONDUCTOR DEVICE AND A METHOD OF FABRICATION	BRASK, JUSTIN K.
10721448	Not Issued	030	11/24/2003	METHOD OF SMOOTHING WAVEGUIDE STRUCTURES	BRASK, JUSTIN K.
10739173	Not Issued	030	12/18/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE THAT INCLUDES A METAL GATE ELECTRODE	BRASK, JUSTIN K.
10742678	Not Issued	019	12/19/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE WITH A METAL GATE ELECTRODE THAT IS FORMED ON AN ANNEALED HIGH-K GATE DIELECTRIC LAYER	BRASK, JUSTIN K.
10746323	Not Issued	041	12/23/2003	METHOD OF FABRICATING SEMICONDUCTOR DEVICES WITH REPLACEMENT, COAXIAL GATE STRUCTURE	BRASK, JUSTIN K.
<u>10748090</u>	Not Issued	092	12/29/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC	BRASK, JUSTIN K.
10748345	Not Issued	030	12/29/2003	METHODS FOR FABRICATING METAL GATE STRUCTURES	BRASK, JUSTIN K.
10748383	Not Issued	030	12/29/2003	METHODS FOR INTEGRATING REPLACEMENT METAL GATE STRUCTURES	BRASK, JUSTIN K.
<u>10748545</u>	Not Issued	030	12/29/2003	METHOD FOR MAKING A SEMICONDUCTOR DEVICE THAT INCLUDES A METAL GATE ELECTRODE	BRASK, JUSTIN K.
10748559	Not Issued	041	12/29/2003	CMOS DEVICE WITH METAL AND SILICIDE GATE ELECTRODES AND A METHOD FOR MAKING IT	BRASK, JUSTIN K.
10749196	Not Issued	030	12/30/2003	REPLACEMENT GATE FLOW FACILITATING HIGH YIELD AND INCORPORATION OF ETCH STOP LAYERS AND/OR STRESSED FILMS	BRASK, JUSTIN K.

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